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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Volker BECKER et al.
Serial No. : 09/762,985
Filed : May 8, 2001
For : DEVICE AND METHOD FOR ETCHING A SUBSTRATE USING
AN INDUCTIVELY COUPLED PLASMA

Art Unit : 1763

Examiner : Luz. L. Alejandro

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Signature: _____

AARON C. DEDITCH
(33,865)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT

SIR:

In response to the Office Action mailed February 27, 2003 (the three-month
response date for which has been extended by one month from May 27, 2003 to June 27,
2003), please reconsider the above-identified application based on the following:

IN THE CLAIMS:

Without prejudice, please amend the claims as follows:

b, 42. (Amended) A method for etching a silicon body substrate using a device having an
ICP source for generating a radio-frequency electromagnetic alternating field, a reactor for
generating an inductively coupled plasma from reactive particles by the action of the radio-
frequency electromagnetic alternating field on a reactive gas, and a first means for generating
plasma power pulses to be injected into the inductively coupled plasma by the ICP source,
comprising:

matching an impedance of one of an inductive coupled plasma and the ICP source to
an ICP coil generator; and

injecting a pulsed radio-frequency power into the inductively coupled plasma as a
pulsed plasma power.

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